



SOT-89 Plastic-Encapsulate Transistors

2SA1213 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.5 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -2 A

Collector-base voltage

$V_{(BR)CBO}$: -50 V

Operating and storage junction temperature range

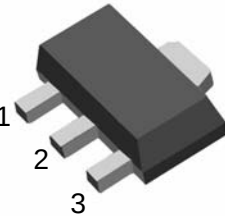
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-50		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1	μA
DC current gain	h_{FE1}	$V_{CE}=-2V, I_C=-0.5A$	70	240	
	h_{FE2}	$V_{CE}=-2V, I_C=-2A$	20		
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-1A, I_B=-0.05A$		-0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=-1A, I_B=-0.05A$		-1.2	V
Transition frequency	f_T	$V_{CE}=-2V, I_C=-0.5A$	100		MHz

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	70-140	120-240

Marking	NO,NY
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